

hollow, said another film being an etch stop for forming the hollow to said predetermined depth.

3. (Thrice Amended) A ferroelectric memory, comprising:  
an insulation film having a hollow at a top surface; and  
a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said hollow, wherein said laminated body includes a lower electrode layer, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer, and said lower electrode layer includes a first electrode portion formed only at a corner of said hollow and a second portion formed on said first electrode portion.